

CD4009M/CD4009C Hex Buffers (Inverting) CD4010M/CD4010C Hex Buffers (Non-Inverting)

General Description

These hex buffers are monolithic complementary MOS (CMOS) integrated circuits. The N- and P-channel enhancement mode transistors provide a symmetrical circuit with output swings essentially equal to the supply voltage. This results in high noise immunity over a wide supply voltage range. No DC power other than that caused by leakage current is consumed during static conditions. All inputs are protected against static discharge. These gates may be used as hex buffers, CMOS to DTL or TTL interface or as CMOS current drivers. Conversion ranges are from 3V to 15V providing $\rm V_{CC} \leq \rm V_{DD}$.

Features

- Wide supply voltage range
- Low power
- High noise immunity
- High current sinking capability

3.0V to 15V 100 nW (typ.)

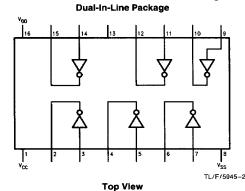
0.45 V_{DD} (typ.)

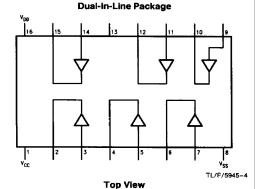
8 mA (min.) at $V_O = 0.5V$ and $V_{DD} = 10V$

Applications

- Automotive
- Data terminals
- Instrumentation
- Medical electronics
- Alarm system
- Industrial controls
- Remote meteringComputers



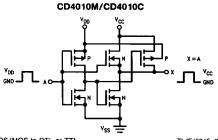




Order Number CD4009* or CD4010*

*Please look into Section 8, Appendix D for availability of various package types.

CD4009M/CD4009C VD0 VCC GND VCC GND VCC GND VCC GND



Hex COS/MOS to DTL or TTL converter (non-inverting).

Connect V_{CC} to DTL or TTL supply. Connect V_{DD} to COS/MOS supply.

TL/F/5945-1

Hex COS/MOS to DTL or TTL converter (inverting).

Connect V_{CC} to DTL or TTL supply. Connect V_{DD} to COS/MOS supply.

TL/F/5945-3

5-33

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Voltage at Any Pin (Note 1) ${\rm V_{SS}} = 0.3 {\rm V} \ {\rm to} \ {\rm V_{SS}} + 15.5 {\rm V}$ Operating Temperature Range

CD40XXM CD40XXC -55°C to +125°C -45°C to +85°C Storage Temperature Range (Ts)

Power Dissipation (P_D)
Dual-In-Line

Dual-In-Line Small Outline -65°C to +150°C

700 mW 500 mW

Lead Temperature (T_L) (Soldering, 10 seconds) Operating Range (V_{DD})

260°C

V_{SS} + 3V to V_{SS} + 15V

DC Electrical Characteristics

Symbol	Characteristics	Test Conditions (Volts)			Limits													
				CD40XXM						CD40XXC								
				−55°C		+ 25°C			+ 125°C		-40°C		+ 25°C		+ 85°C		Units	
		Vo	V _{DD}	Min	Max	Min	Тур	Max	Min	Max	Min	Max	Min	Тур	Max	Min	Max	
lcc	Quiescent Device Current		5 10		0.3 0.5		0.01 0.01	0.3 0.5		20 30		3 5		0.03 0.05	- 1		42 70	μA μA
PD	Quiescent Device Dissipation/Package		5 10		1.5 5		0.05 0.1	1.5 5		100 300		15 50		0.15 0.5	15 50		210 700	μW
~~	Output Voltage Low Level High Level		5 10 5 10		0.01 0.01	4.99 9.99	0 0 5 10	0.01 0.01		0.05 0.05		0.01 0.01	4.99 9.99	_	0.01 0.01		0.05 0.05	٧
	Noise Immunity (All Inputs)																	
V _{NL}	СD4009М {	$V_O \ge 4.0$ $V_O \ge 8.0$	5 10	1 2		1 2	2.25 4.5		0.9 1.9		1 2		1 2	2.25 4.5		0.9 1.9		V
V _{NL}	CD4010M {	$V_O \ge 1.5$ $V_O \ge 3.0$	5 10	1.6 3.2		1.5 3	2.25 4.5		1.4 2.9		1.6 3.2		1.5 3	2.25 4.5		1.4 2.9		V V
V _{NH}		$V_O \ge 3.5$ $V_O \ge 7.0$	5 10	1.4 2.9		1.5 3	2.25 4.5		1.5 3		1.4 2.9		1.5 3	2.25 4.5		1.5 3		V
I _D N	Output Drive Current N-Channel (Note 2) P-Channel (Note 2)	0.4 0.5 2.5 9.5	5 10 5 10	3.75 10 -1.85 -0.9		3 8 1.25 0.6	4 10 -1.75 -0.8		2.1 5.6 -0.9 -0.4		3.6 9.6 -1.5 -0.72		3 8 -1.25 -0.6			2.4 6.4 -1 -0.48		mA mA mA
liN	Input Current						10							10				pΑ

Note 1: This device should not be connected to circuits with the power on because high transient voltage may cause permanent damage Note 2: I_DN and I_DP are tested one output at a time.

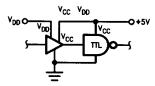
AC Electrical Characteristics*

 $T_A = 25$ °c, $C_L = 15$ pF, unless otherwise noted. Typical Temperature coefficient for all values of $V_{DD} = 0.3\%$ °C

	Test	Limits								
Characteristics	Conditi		CD40XX	A		Units				
		V _{DD} (Volts)	Min	Тур	Max	Min	Тур	Max	1 Julies	
Propagation Delay Time:	V _{CC} = V _{DD}	5	_	15	55	_	15	70		
High-to-Low Level (t _{PHL})	1	10		10	30	_	10	40		
	$V_{DD} = 10V$ $V_{CC} = 5V$		_	10	25	_	10	35	ns	
Low-to-High Level (tpLH)	$V_{CC} = V_{DD}$	5 10	_	50	80		50	100		
-ou to riight zoto. (tp[H)			—	25	55	_	25	70		
-	$V_{DD} = 10V$ $V_{CC} = 5V$		_	15	30	-	15	40	ns	
Transition Time:	V V	5	_	20	45		20	60	ns	
High-to-Low Level (t _{THL})	V _{CC} = V _{DD}	10	_	16	40	_	16	50		
Low-to-High Level (t _{TLH})	$V_{CC} = V_{DD}$	5 10	_	80 50	125 100	_	80 50	160 120	ns	
Input Capacitance (C _i)	Any Input		_	5	_	_	5	_	рF	

5-34

Typical Application



TL/F/5945-5